Am100480

16,384 x 1 IMOXTM ECL Bipolar RAM

PRELIMINARY

DISTINCTIVE CHARACTERISTICS

- Fast access time (15 ns) improves system cycle speeds.
- Enhanced output voltage level compensation providing 6X (improvement in) V_{OL} and V_{OH} stability over supply and temperature ranges.
- Internally voltage and temperature compensated providing flat AC performance.
- Fully compatible with 100K series ECL logic no board changes required.
- Emitter follower outputs easy wire-ORing
- Power dissipation decreases with increasing temperature.

GENERAL DESCRIPTION

The Am100480-15 and Am100480-25 are fully decoded 16,384-bit ECL RAMs organized 16,384 words by one bit. Bit selection is achieved by means of a 14-bit address, A_0 through A_{13} . Easy memory expansion is provided by an active LOW chip select ($\overline{\text{CS}}$) input and an unterminated OR tieable emitter follower output.

An active LOW write enable (WE) controls the write/read operation of the memory. When the chip select and write

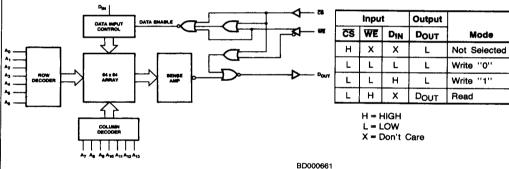
enable lines are LOW, the data input ($D_{\mbox{\scriptsize IN}}$) is written into the addressed memory word.

Reading is performed with the chip select line LOW and the write enable line HIGH. The information stored in the addressed bit is read out on the noninverting output (DOUT).

During the writing operation, or when the chip select line is HIGH, the output of the memory goes to a LOW state.



MODE SELECT TABLE



PRODUCT SELECTOR GUIDE

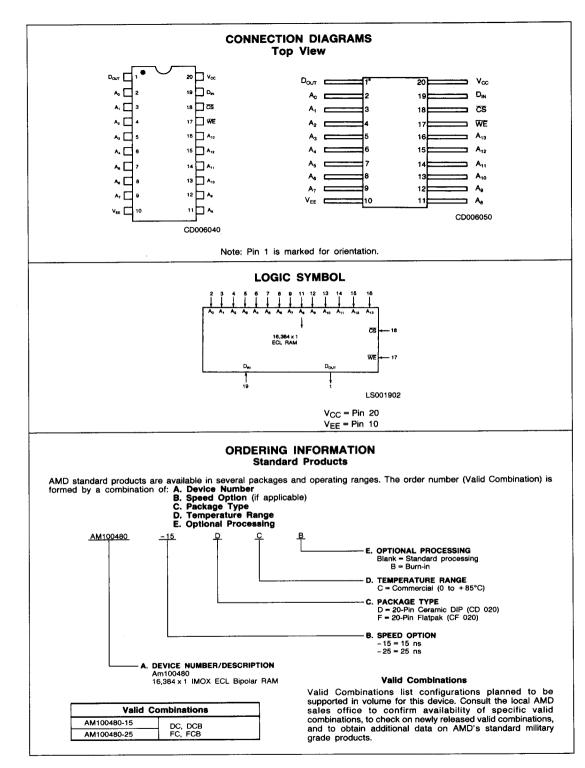
Highlights of Key Performance Parameters (Commercial)

Part Number	Am 100480-15	Am100480-25
Address Access Time (t _{AA})	15 ns	25 ns
Write Pulse Width (tw)	15 ns	25 ns
Write Recovery (twn)	18 ns	20 ns
Chip Select Access/ Recovery and Write Disable Times (t _{ACS} , t _{RCS} , t _{WS})	8 ns	10 ns
Power Supply (I _{EE})	220 mA	200 mA

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ABSOLUTE MAXIMUM RATINGS

Storage Temperature65 to +150°C
Case Temperature with
Power Applied55 to +125°C
VEE Pin Potential to GND Pin7.0 V to +0.5 V
Input Voltage (DC)VEE to +0.5 V
Output Current (DC Output HIGH)30 mA to +0.1 mA

Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES

Commercial (C) Devices (Note 2)		
Temperature 0	to	+85°C
Supply Voltage5.7 V	to	-4.2 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS V_{EE} = -4.5 V, V_{CC} = GND (Note 2)

Parameter Symbol	Parameter Description	Test Conditions (Note 2)		B (Note 3)	Typ. (Note 1)	A (Note 3)	Units
Voн	Output Voltage HIGH	VIN = VIHA OF VILB	IN # VILLA OF VILD		-955	-880	mV
VOL	Output Voltage LOW	THE THE O' TILB	Loading is	- 1810	-1715	- 1620	mV
Vонс	Output Voltage HIGH	VIN = VIHB OF VILA	50 Ω to -2.0 V	-1035			mV
Volc	Output Voltage LOW	TIN TINE OF TILA		- 6		-1610	mV
VIH	Input Voltage HIGH	Guaranteed Input Voltag (Note 4)	e HIGH for All Inputs	-1165		-880	mV
VIL	Input Voltage LOW	Guaranteed Input Veltag (Note 4)		-1810		-1475	mV
lн	Input Current HIGH	Vin WVIHA		1		220	μΑ
L	Input Current LOW Chip Select (CS)	V _{IN} = V _{ILB}		0.5		170	
հ ե	All Other Inputs			-50			μΑ
lee	Power Supply	All Inputs and	Am100480-15	-220			
JEE .	Current (Pin 10)	Outputs Open	Am100480-25	-200	-		mA

Notes: 1. Typical values are:

- Typical values are:
 VEC = -4.5 V, VCC = GND, T_A = 25°C
 Output Load = 50 Ω and 30 pF to -2.0 V, T_A = 0 to +85°C for DIPs. Guaranteed with transverse air flow exceeding 400 linear F.P.M. and 2-minute warm-up period. Approximate resistance values of the package are: $\theta_{\rm JA}$ (Junction-to-Ambient) = 90°C/Watt (still air)
 - θ_{JA} (Junction-to-Ambient) = 50°C/Watt (at 400 F.P.M. air flow)
 - TC = 0 to +85°C for Flatpak and LCC packages

θ_{JC} (Junction-to-Case) = 25°C/Watt

- Definition of symbols and terms used in this product specification: The relative values of the specified conditions and limits will be referenced to an algebraic scale. The extremities of the scale are: "A" the value closest to positive infinity, "B" the value closest to negative infinity.
 These are absolute voltages with respect to device ground pin and include all overshoots due to system and/or tester noise. Do not attempt to test these values without suitable equipment.

				A	m100480-	15	А	m100480-	25	
No.	Parameter Symbol	Parameter Description	Test Conditions	Min.	Typ. (Note 1)	Max.	Min.	Typ. (Note 1)	Max.	Unite
REA	MODE									
1	t _{ACS}	Chip Select Access Time	Manager of EON of			8			10	
2	tRCS	Chip Select Recovery Time	Measured at 50% of input to 50% of output	ļ		8	্ৰক্টেপ্টিল	- 107 - 107	10 25	ns
3	taa	Address Access Time		<u> </u>						ш
VRIT	E MODE	1 D. 1	·	T		100 G	p. 63636303	-	т —	
4	tw	Write Pulse Width (to Guarantee Writing)	twsa = twsa (Min.)	15			25			ns
5	twsp	Data Setup Time Prior to Write		2.	4 2 4	,	5			ns
6	twHD	Data Hold Time After Write		.3			5			ns
7	twsa	Address Setup Time Prior to Write	tw = tw (Min.)	2			5			ns
8	twha	Address Hold Time After Write		3			5	-		ns
9	twscs	Chip Select Setup Time		2			5			ns
10		Prior to Write Chip Select Hold Time	Measured at 50% of	3	-		5			ns
	twics	After Write Write Disable Time	input to 50% of output	<u> </u>	 	В	\vdash		10	ns
11	tws	Write Recovery Time	4		-	18		 	20	ns
	TIME AND			I	<u> </u>			I	<u> </u>	
IISE	t _r	Output Rise Time	Measured between		2.5	<u> </u>	T .	2.5		
12		Output The Time	20% and 80% points					2.5		ns
		Output Fall Time	20% and 60% points	1	1 2.5	}				
_	t _f	Output Fall Time	20% and 80% points	l	2.5	l		2.0	<u> </u>	
14 CAP	t _f ACITANCE			I	·		<u> </u>			
14 CAP/ 15	t _f	Input Pin Capacitance Output Pin Capacitance	Measure with a pulse technique on sample basis TCHING WAVEFO	DRMS	7	.)		4 7		pF
14 CAP/ 15 16	ti ACITANCE CIN COUT	Input Pin Capacitance Output Pin Capacitance	Measure with a pulse technique on sample basis	DRMS	7		PORESS L	4 7		pF
14 CAP/ 15 16	tr ACITANCE Cin COUT	Input Pin Capacitance Output Pin Capacitance SWI	Measure with a pulse technique on sample basis	DRMS	7		DORESS L	4 7		
14 CAP/ 15 16	tr ACITANCE CIN COUT DDRESS AgrAs	Input Pin Capacitance Output Pin Capacitance SWI	Measure with a pulse technique on sample basis	DRMS	7		DORESS	4 7		50%
14 CAP/ 15 16	ty ACITANCE CIN COUT COUT COUT COUT	Input Pin Capacitance Output Pin Capacitance SWI	Measure with a pulse technique on sample basis TCHING WAVEFO	DRMS	(Cont'd		DORESS L	4 7		50%
14 CAP/ 15 16	CIN COUT	Input Pin Capacitance Output Pin Capacitance SWI ADDRESS J	Measure with a pulse technique on sample basis TCHING WAVEFO ADDRESS K	DRMS	(Cont'd	AC	DORESS L	4 7		50%
14 CAP/ 15 16	CS CITANCE CIN COUT COUT CS CS CS	Input Pin Capacitance Output Pin Capacitance SWI	Measure with a pulse technique on sample basis TCHING WAVEFO	DRMS	(Cont'd		DORESS L	4 7	ĒΟ	50%

